

NPN RF POWER TRANSISTOR

DESCRIPTION:

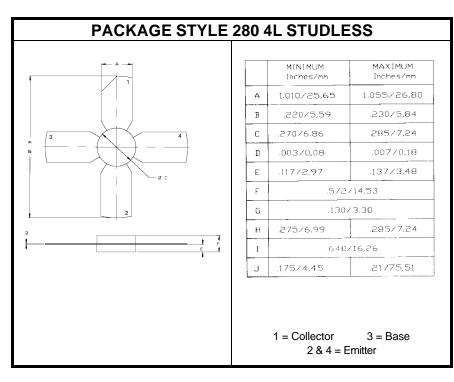
The **ASI SRF 1136** is a Common Emitter Device Designed for class C Amplifier Applications up to 1 GHz.

FEATURES INCLUDE:

- High Gain
- Gold Metallization
- Emitter Ballasting

MAXIMUM RATINGS

Ιc	800 mA			
V_{CBO}	36 V			
P _{DISS}	19 W @ $T_{C} = 25 {}^{O}C$			
ΤJ	-55 ^o C to +200 ^o C			
T _{STG}	-55 ^o C to +150 ^o C			
đ ic	7.5 ⁰ C/W			



CHARACTERISTICS $T_c = 25 °C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV _{CBO}	$I_c = 10 \text{ mA}$	36			V
BV _{CEO}	$I_c = 20 \text{ mA}$	16			V
BV_{EBO}	I _E = 1 mA	3.0			V
h _{FE}	$V_{CE} = 10 \text{ V}$ $I_{C} = 600 \text{ mA}$	25	100		
Сов	V _{CB} = 12.5 V f = 1.0 MHz		5		рF
*P _G					dB
* h c					%

* RF SPECIFICATIONS ARE CONTROLLED BY CUSTOMER DRAWING AND ARE PROPRIETARY.

ADVANCED SEMICONDUCTOR, INC.

7525 ETHEL AVENUE • NORTH HOLLYWOOD, CA 91605 • (818) 982-1200 • FAX (818) 765-3004